

Silicon NPN Power Transistors

BUW13F BUW13AF

DESCRIPTION

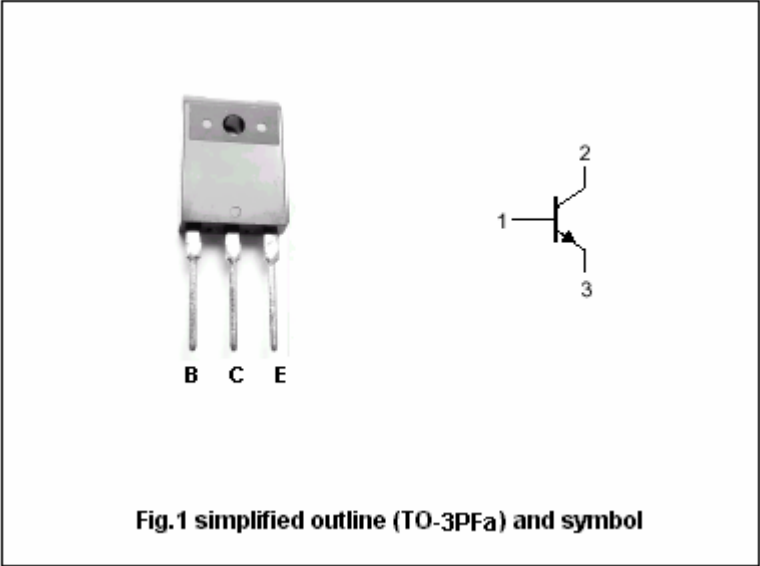
- With TO-3PFa package
- High voltage;high speed

APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor control systems

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	BUW13F	Open emitter	850	V
		BUW13AF		1000	
V_{CEO}	Collector-emitter voltage	BUW13F	Open base	400	V
		BUW13AF		450	
V_{EBO}	Emitter-base voltage		Open collector	9	V
I_C	Collector current			15	A
I_{CM}	Collector current-peak			30	A
I_B	Base current			6	A
I_{BM}	Base current-peak			9	A
P_T	Total power dissipation		$T_C=25^{\circ}C$	50	W
T_j	Junction temperature			150	$^{\circ}C$
T_{stg}	Storage temperature			-65~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-a}$	Thermal resistance from junction to ambient	35	K/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	BUW13F	I _C =0.1A ; I _B =0; L=25mH	400			V
		BUW13AF		450			
V _{CEsat}	Collector-emitter saturation voltage	BUW13F	I _C =10A; I _B =2A			1.5	V
		BUW13AF	I _C =8A; I _B =1.6A				
V _{BEsat}	Base-emitter saturation voltage	BUW13F	I _C =10A; I _B =2A			1.6	V
		BUW13AF	I _C =8A; I _B =1.6A				
I _{CES}	Collector cut-off current		V _{CE} =Rated V _{CES} ; V _{BE} =0 T _j =125°C			1.0 4.0	mA
I _{EBO}	Emitter cut-off current		V _{EB} =9V; I _C =0			10	mA
h _{FE-1}	DC current gain		I _C =20mA ; V _{CE} =5V	10		35	
h _{FE-2}	DC current gain		I _C =1.5A ; V _{CE} =5V	10		35	

Switching times resistive load

t _{on}	Turn-on time	For BUW13F I _C =10A ; I _{B1} =-I _{B2} =-2A For BUW13AF I _C =8A ; I _{B1} =-I _{B2} =-1.6A			1.0	μs
t _s	Storage time				4.0	μs
t _f	Fall time				0.8	μs

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PACKAGE OUTLINE

